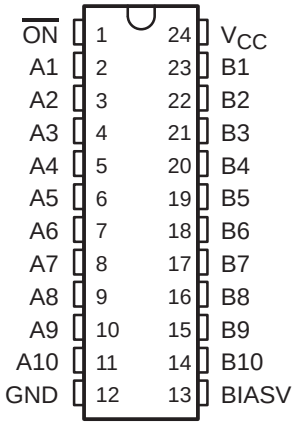
- **5-Ω Switch Connection Between Two Ports**
- **TTL-Compatible Input Levels**
- **Outputs Are Precharged by Bias Voltage to Minimize Signal Distortion During Live Insertion**
- **Schottky Diodes on the I/Os to Clamp Undershoots up to –2 V**
- **Package Options Include Plastic Shrink Small-Outline (DB, DBQ), Thin Very Small-Outline (DGV), Small-Outline (DW), and Thin Shrink Small-Outline (PW) Packages**

DB, DBQ, DGV, DW, OR PW PACKAGE
(TOP VIEW)



description

The SN74CBTS6800 provides ten bits of high-speed TTL-compatible bus switching with Schottky diodes on the I/Os to clamp undershoot.

The low on-state resistance of the switch allows bidirectional connections to be made, while adding near-zero propagation delay. The device also precharges the B port to a user-selectable bias voltage (BIASV) to minimize live-insertion noise.

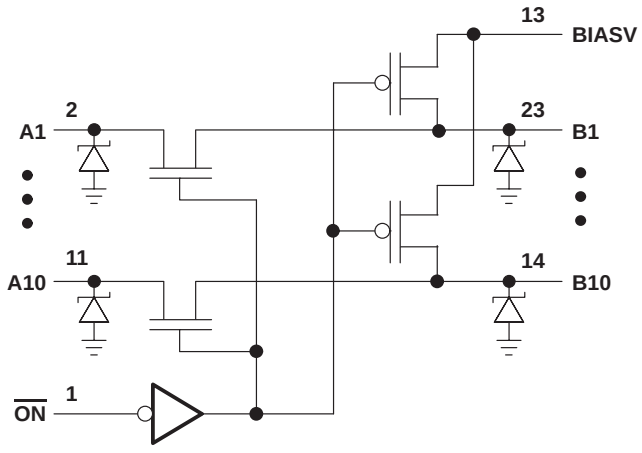
The SN74CBTS6800 is organized as one 10-bit switch with a single enable ($\overline{ON}$) input. When $\overline{ON}$ is low, the switch is on, and port A is connected to port B. When $\overline{ON}$ is high, the switch between port A and port B is open. When $\overline{ON}$ is high or V_{CC} is 0 V, B port is precharged to BIASV through the equivalent of a 10-kΩ resistor.

The SN74CBTS6800 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

$\overline{ON}$	B1–B10	FUNCTION
L	A1–A10	Connect
H	BIASV	Precharge

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 7 V
Bias voltage range, BIASV . . . . . –0.5 V to 7 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Continuous channel current . . . . . 128 mA
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 2): DB package . . . . . 63°C/W
DBQ package . . . . . 61°C/W
DGV package . . . . . 86°C/W
DW package . . . . . 46°C/W
PW package . . . . . 88°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 3)

		MIN	MAX	UNIT
V_{CC}	Supply voltage	4	5.5	V
BIASV	Supply voltage	1.3	V_{CC}	V
V_{IH}	High-level control input voltage	2		V
V_{IL}	Low-level control input voltage		0.8	V
T_A	Operating free-air temperature	–40	85	°C

NOTE 3: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP‡	MAX	UNIT
V_{IK}	A or B inputs	V_{CC} = 4.5 V,	I_I = –18 mA				–0.7	V
	Control inputs						–1.2	
I_{IL}		V_{CC} = 5.5 V,	V_I = GND				–5	µA
I_{IH}		V_{CC} = 5.5 V,	V_I = 5.5 V				150	µA
I_O		V_{CC} = 4.5 V,	BIASV = 2.4 V,	V_O= 0	0.25			mA
I_{CC}		V_{CC} = 5.5 V,	I_O = 0,	V_I = V_{CC} or GND			3	µA
ΔI_{CC}§	Control inputs	V_{CC} = 5.5 V,	One input at 3.4 V,	Other inputs at V_{CC} or GND			2.5	mA
C_i	Control inputs	V_I = 3 V or 0				3.5		pF
$C_{io(OFF)}$		V_O = 3 V or 0,	$\overline{ON}$ = V_{CC}			4.5		pF
r_{on}¶		V_{CC} = 4 V, TYP at V_{CC} = 4 V	V_I = 2.4 V,	I_I = 15 mA		11	20	Ω
		V_{CC} = 4.5 V	V_I = 0	I_I = 64 mA		3	7	
				I_I = 30 mA		3	7	
			V_I = 2.4 V,	I_I = 15 mA		6	15	

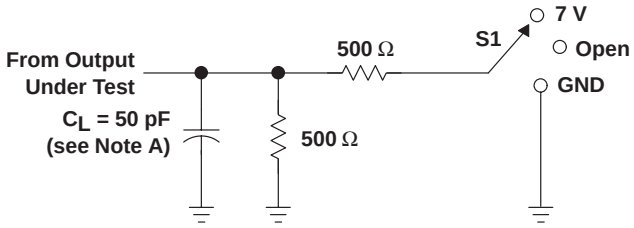
‡ All typical values are at V_{CC} = 5 V (unless otherwise noted), T_A = 25°C.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.
¶ Measured by the voltage drop between the A and B terminals at the indicated current through the switch. On-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	TEST CONDITIONS	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 4 V		V_{CC} = 5 V ± 0.5 V		UNIT
				MIN	MAX	MIN	MAX	
t_{pd}†		A or B	B or A		0.35		0.25	ns
t_{PZH}	BIASV = GND	$\overline{ON}$	A or B		6	2	5.1	ns
t_{PZL}	BIASV = 3 V				6	2	5.6	
t_{PHZ}	BIASV = GND	$\overline{ON}$	A or B		5.5	1	5	ns
t_{PLZ}	BIASV = 3 V				5.5	2	5.9	

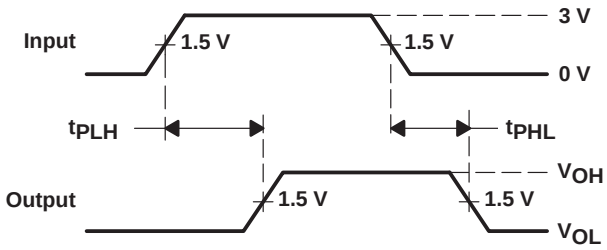
† The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

PARAMETER MEASUREMENT INFORMATION

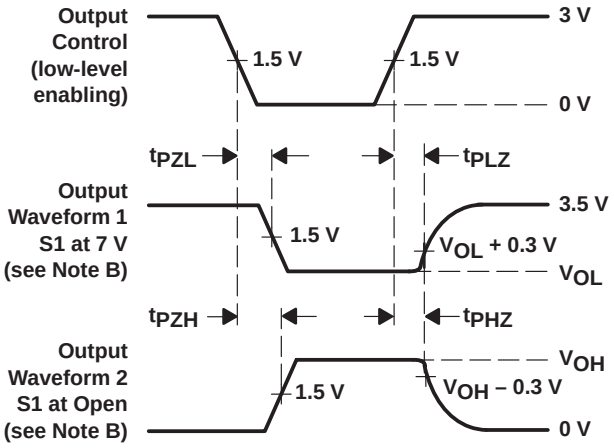


LOAD CIRCUIT

TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	7 V
t_{PHZ}/t_{PZH}	Open



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

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